## NSN 5961-00-906-7876

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-906-7876 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 4.5 gate trigger voltage, dc and 2.0 on-state voltage, dc **Current Rating Per Characteristic:** 16.00 amperes forward current, total rms nanoamperes and 500.00 milliamperes forward current, total rms preset **Maximum Operating Tempurature Per Measurement Point:** 70.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 80131-release4957 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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